COMPLIANT

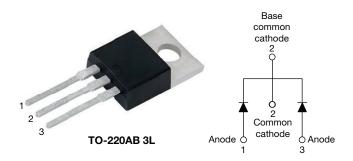
HALOGEN



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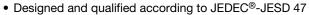
Hyperfast Rectifier, 2 x 15 A FRED Pt®



PRIMARY CHARACTERISTICS								
I _{F(AV)}	2 x 15 A							
V_{R}	300 V							
V _F at I _F	0.85 V							
t _{rr} typ.	See Recovery table							
T _J max.	175 °C							
Package	TO-220AB 3L							
Circuit configuration	Common cathode							

FEATURES

- · Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current





DESCRIPTION / APPLICATIONS

300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diodes in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Peak repetitive reverse voltage		V_{RRM}		300	V				
Average rectified forward current	per diode		T _C = 153 °C	15					
Average rectilled forward current	per device	I _{F(AV)}		30	Α				
Non-repetitive peak surge current	I _{FSM}	T _C = 25 °C	150						
Operating junction and storage tem	T _J , T _{Stg}		-65 to +175	°C					

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	Ι _R = 100 μΑ	300	-	-	.,				
Famous de la casa	V _F	I _F = 15 A	-	1.0	1.25	V				
Forward voltage		I _F = 15 A, T _J = 125 °C	-	0.85	0.95					
Povoros loskago ourrent		$V_R = V_R$ rated	-	-	40					
Reverse leakage current	I _R	$T_J = 125$ °C, $V_R = V_R$ rated	-	8	200	μA				
Junction capacitance C_T $V_R = 300 \text{ V}$		-	38	=	pF					
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nΗ				

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DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
		$I_F = 1 A, dI_F/dt = 50$	ı	ı	36					
Reverse recovery time	t _{rr}	$I_F = 1 A, dI_F/dt = 10$	-	-	30	ns				
		T _J = 25 °C		-	33	-	115			
		T _J = 125 °C		-	48	-				
Peak recovery current	I _{RRM}	T _J = 25 °C	l _F = 15 A dl _F /dt = 200 A/μs	-	2.8	-	۸			
			$V_{\rm R} = 200 \text{ V}$	-	6.5	-	Α			
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	46	-	200			
		T _J = 125 °C		-	160	-	nC			

THERMAL MECHANICAL SPECIFICATIONS										
PARAMETER SYMBOL MIN. TYP. MAX. UNITS										
Maximum junction and storage temperature range	T _J , T _{Stg}	-65	=	175	°C					
Thermal resistance, junction to case per diode	R_{thJC}	-	-	1.4	°C/W					
Marking device Case style TO-220AB 3L 30CTH03										

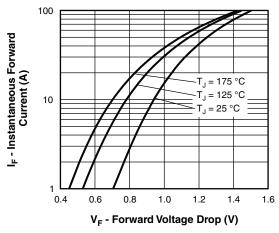


Fig. 1 - Typical Forward Voltage Drop Characteristics

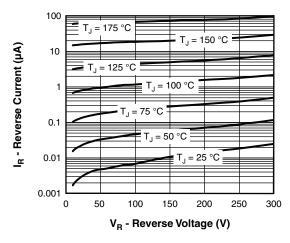


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

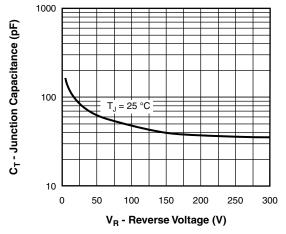


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

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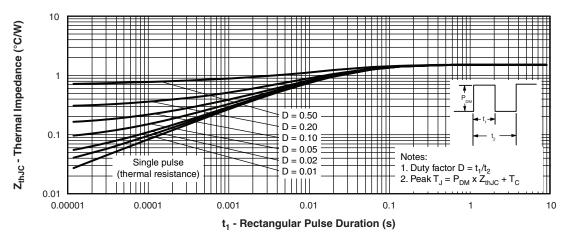


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

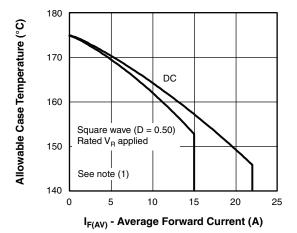


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

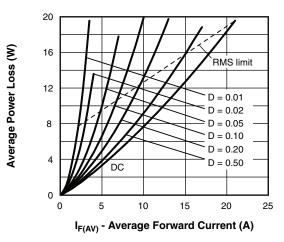


Fig. 6 - Forward Power Loss Characteristics

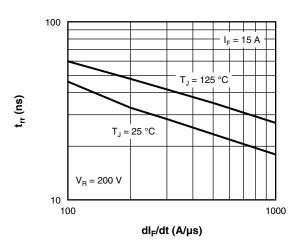


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

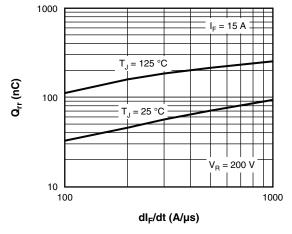


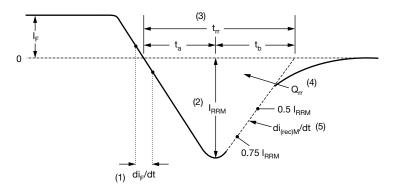
Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); Pd_{REV} = inverse power loss = $V_{R1} \times I_R$ (1 - D); I_R at V_{R1} = rated V_R

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- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm l_{r}$ to point where a line passing through 0.75 $\rm l_{RRM}$ and 0.50 $\rm l_{RRM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

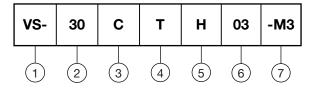
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- Current rating (30 = 30 A)
- 3 Circuit configuration:

C = common cathode

4 - Package:

T = 3L TO-220AB

5 - H = hyperfast recovery

6 - Voltage rating (03 = 300 V)

7 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

ORDERING INFORMATION (Example)									
PREFERRED P/N BASE QUANTITY PACKAGING DESCRIPTION									
VS-30CTH03-M3	50	Antistatic plastic tubes							

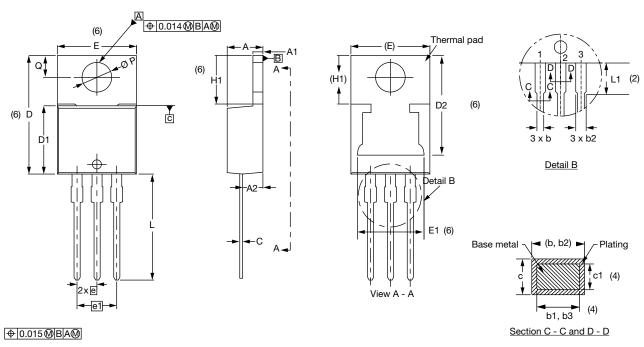
LINKS TO RELATED DOCUMENTS							
Dimensions <u>www.vishay.com/doc?96154</u>							
Part marking information	www.vishay.com/doc?95028						

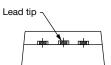
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TO-220AB 3L

DIMENSIONS in millimeters and inches





Conforms to JEDEC® outline TO-220AB

SYMBOL	MILLIN	IETERS	INC	HES	NOTES		SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183			D2	11.68	13.30	0.460	0.524	6, 7
A1	1.14	1.40	0.045	0.055			Е	10.11	10.51	0.398	0.414	3, 6
A2	2.50	2.92	0.098	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			е	2.41	2.67	0.095	0.105	
b1	0.38	0.97	0.015	0.038	4		e1	4.88	5.28	0.192	0.208	
b2	1.20	1.73	0.047	0.068			H1	6.09	6.48	0.240	0.255	6
b3	1.14	1.73	0.045	0.068	4		L	13.52	14.02	0.532	0.552	
С	0.36	0.61	0.014	0.024			L1	3.32	3.82	0.131	0.150	2
c1	0.36	0.56	0.014	0.022	4		ØΡ	3.54	3.91	0.139	0.154	
D	14.85	15.35	0.585	0.604	3		Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355							•	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- $^{(7)}$ Outline conforms to JEDEC $^{\!(\!R\!)}$ TO-220, except D2

Revision: 14-Mar-2022 1 Document Number: 96154

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